

# **BT162 SERIES**

## SILICON BIDIRECTIONAL THYRISTORS

### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage			
(T <sub>J</sub> = -40 to 110°C, half sine wave, 50 to 60Hz, gate open)	$V_{DRM}$		Volts
BT162-400	<b>V</b> DRM	400	VOILS
BT162-600		600	
Non-repetitive peak off-state voltage			
$(T_J = -40 \text{ to } +110^{\circ}\text{C}, \text{ t} \le 10 \text{ms, gate open})$	$V_{DSM}$		Volts
BT162-400	<b>V</b> DSM	500	VOILS
BT162-600		700	
RMS on-state current			
(full cycle sine wave 50 to 60Hz)			Amps
$(T_C = 80^{\circ}C)$	I <sub>T(RMS)</sub>	12.0	Allips
(T <sub>C</sub> = 95°C)		6.0	
Peak surge current			
(1 cycle, $T_C = 80$ °C, preceded and followed by rated current)	I <sub>TSM</sub>		Amps
60Hz	ITSM	120	Allips
50Hz		110	
Rate of rise of on-state current (gate open, non-repetitive)	di <sub>⊤</sub> /dt	10	A/μs
Circuit fusing considerations ( $T_J = -40 \text{ to } 110^{\circ}\text{C}$ , $t = 1.0 \text{ to } 10 \text{ms}$ )	I <sup>2</sup> t	40	A <sup>2</sup> s
Peak gate voltage	V <sub>GM</sub>	10	Volts
Peak gate current	I <sub>GM</sub>	2.0	Amps
Peak gate power ( $T_c = 80^{\circ}$ C, pulse width = 2.0 $\mu$ s)	P <sub>GM</sub>	20	Watts
Average gate power (T <sub>C</sub> = 80°C, t = 10ms)	$P_{G(AV)}$	0.5	Watts
Operating junction temperature range	T,	-40 to +110	°C
Storage temperature range	T <sub>stg</sub>	-40 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	R <sub>eJC</sub>	2.0	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур.	Max	Unit
Peak blocking current (either direction)					A
(Rated V <sub>DRM</sub> @ T <sub>J</sub> = 110°C, gate open)	I <sub>DRM</sub>	-	-	2.0	mA
Peak on-state voltage (either direction)	V				Volts
$(I_{TM} = 17A \text{ peak, pulse width} = 1 \text{ to } 2\text{ms, duty cycle} \le 2\%)$	V <sub>TM</sub>	-	1.3	1.75	VOILS
Gate trigger current (continuous dc)					
(main terminal voltage = 12V, $R_L$ = 100 $\Omega$ , minimum gate pulse width = 2.0 $\mu$ s)					
MT2(+), G(-)	I <sub>GT</sub>	-	25	40	mA
MT2(-), G(-)		-	20	40	
MT2(+), G(-); MT2(-), G(-), $T_C = -40^{\circ}C$		-	-	75	



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dv/dt

V/μ

100

Gate trigger voltage (continuous dc)							
(main terminal voltage = 12V, $R_L$ = 100 $\!\Omega$ , minimum gate pulse width = 2.0 $\!\mu s$ )							
MT2(+), G(-)		-	0.9	1.5			
MT2(-), G(-)	$V_{GT}$	-	1.1	1.5	Volts		
MT2(+), G(-); MT2(-), G(-), T <sub>c</sub> = -40°C		-	-	2.0			
(main terminal voltage = rated $V_{DRM}$ , $R_L = 10k\Omega$ , $T_J = 110^{\circ}C$ )							
MT2(+), G(-); MT2(-), G(-)		0.2	-	-			
Holding current (either direction)							
(main terminal voltage= 12V, gate open, initiating current = 200mA)							m A
T <sub>C</sub> = 25°C			I <sub>H</sub>	-	6.0	30	mA
$T_C = -40$ °C				-	-	50	
Latching current							
(main terminal voltage = 12V, $R_L$ = variable, gate pulse width = 20 $\mu$ s, duty cycle $\leq$ 2%)							
MT2(+), G(-) @ I <sub>GT</sub> = 40mA				-	30	60	mA
MT2(-), G(-) @ I <sub>GT</sub> = 40mA			Iι	-	6.0	40	mA
MT2(+), G(-) @ $I_{GT}$ = 75mA, $T_C$ = -40°C				-	-	100	
MT2(-), G(-) @ $I_{GT}$ = 75mA, $T_C$ = -40°C				-	-	60	

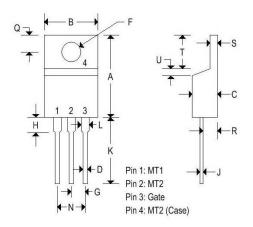
Note 1: Off state voltage up to 800V may be applied, but triac may switch into the on-state. In that case, the rate of rise of on-state current should not exceed its specified maximum rating.

#### MECHANICAL CHARACTERISTICS

Critical rate of rise of off-state voltage

Case	TO-220AB
Marking	Alpha-numeric
Pin out	See below

(Rated  $V_{DRM}$ , exponential voltage rise, gate open,  $T_C = 110$ °C)

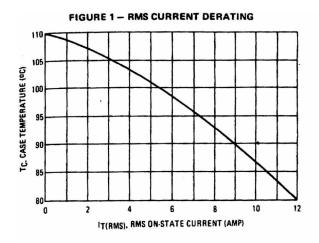


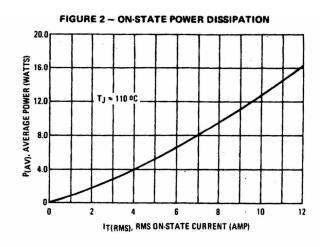
		TO-2	220AB		
	Inc	hes	Millimeters		
	Min	Max	Min	Max	
Α	0.575	0.620	14.600	15.750	
В	0.380	0.405	9.650	10.290	
С	0.160	0.190	4.060	4.820	
D	0.025	0.035	0.640	0.890	
F	0.142	0.147	3.610	3.730	
G	0.095	0.105	2.410	2.670	
Н	0.110	0.155	2.790	3.930	
J	0.014	0.022	0.360	0.560	
K	0.500	0.562	12.700	14.270	
L	0.045	0.055	1.140	1.390	
N	0.190	0.210	4.830	5.330	
Q	0.100	0.120	2.540	3.040	
R	0.080	0.110	2.040	2.790	
S	0.045	0.055	1.140	1.390	
T	0.235	0.255	5.970	6.480	
U	12	0.050	197	1.270	
٧	0.045	(4)	1.140	(2)	
Z	-	0.080	-	2.030	

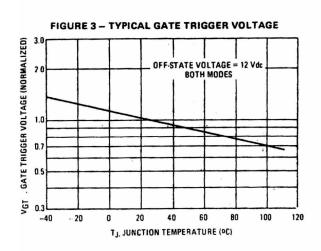


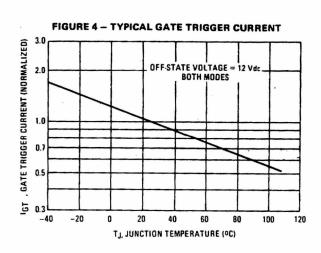
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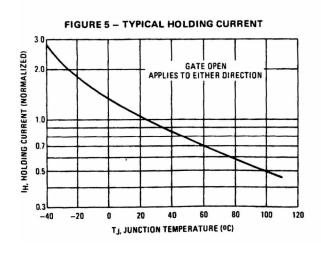
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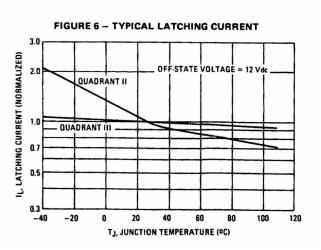










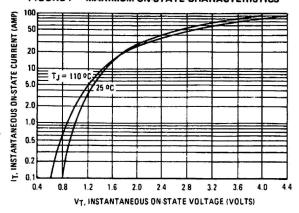




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### FIGURE 7 - MAXIMUM ON-STATE CHARACTERISTICS



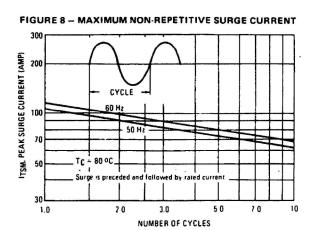


FIGURE 9 – TYPICAL THERMAL RESISTANCE FROM MOUNTING BASE TO HEATSINK

Metal to Metal:	Dry	0,9 °C/W
Metal to Metal:	Lubed	0,3 °C/W
With Insulator:	Dry	Not recommended
With Insulator:	Lubed	1,3 °C/W

These values are available when using the rectangular washer and mica insulator furnished with the kit MK221-2. The recommended mounting torque is 8 Kg. cm.

## FIGURE 10 - THERMAL RESPONSE

